

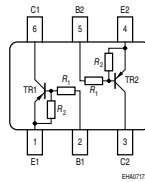
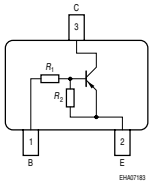
PNP Silicon Digital Transistor

- Switching circuit, inverter, interface circuit, driver circuit
- Built in bias resistor ($R_1 = 47k\Omega$, $R_2 = 47k\Omega$)
- For 6-PIN packages: two (galvanic) internal isolated transistors with good matching in one package



**BCR198/F/L3
BCR198T/W**

**BCR198S
SEMB2**



| Type | Marking | Pin Configuration | | | | | | Package |
|----------|---------|-------------------|------|------|------|------|------|----------|
| | | 1=B | 2=E | 3=C | - | - | - | |
| BCR198 | WRs | 1=B | 2=E | 3=C | - | - | - | SOT23 |
| BCR198F | WRs | 1=B | 2=E | 3=C | - | - | - | TSFP-3 |
| BCR198L3 | WR | 1=B | 2=E | 3=C | - | - | - | TSLP-3-4 |
| BCR198S | WRs | 1=E1 | 2=B1 | 3=C2 | 4=E2 | 5=B2 | 6=C1 | SOT363 |
| BCR198T | WRs | 1=B | 2=E | 3=C | - | - | - | SC75 |
| BCR198W | WRs | 1=B | 2=E | 3=C | - | - | - | SOT323 |
| SEMB2 | WR | 1=E1 | 2=B1 | 3=C2 | 4=E2 | 5=B2 | 6=C1 | SOT666 |

Maximum Ratings

| Parameter | Symbol | Value | Unit |
|--|-------------|---|------|
| Collector-emitter voltage | V_{CEO} | 50 | V |
| Collector-base voltage | V_{CBO} | 50 | |
| Emitter-base voltage | V_{EBO} | 10 | |
| Input on voltage | $V_{i(on)}$ | 50 | |
| Collector current | I_C | 70 | mA |
| Total power dissipation- BCR198, $T_S \leq 102^\circ\text{C}$ BCR198F, $T_S \leq 128^\circ\text{C}$ BCR198L3, $T_S \leq 135^\circ\text{C}$ BCR198S, $T_S \leq 115^\circ\text{C}$ BCR198T, $T_S \leq 109^\circ\text{C}$ BCR198W, $T_S \leq 124^\circ\text{C}$ SEMB2, $T_S \leq 75^\circ\text{C}$ | P_{tot} | 200 250 250 250 250 250 250 | mW |
| Junction temperature | T_j | 150 | °C |
| Storage temperature | T_{stg} | -65 ... 150 | |

Thermal Resistance

| Parameter | Symbol | Value | Unit |
|--|------------|-------|------|
| Junction - soldering point ¹⁾ | R_{thJS} | | K/W |
| BCR198 | | ≤ 240 | |
| BCR198F | | ≤ 90 | |
| BCR198L3 | | ≤ 60 | |
| BCR198S | | ≤ 140 | |
| BCR198T | | ≤ 165 | |
| BCR198W | | ≤ 124 | |
| SEMB2 | | ≤ 300 | |

¹For calculation of R_{thJA} please refer to Application Note Thermal Resistance

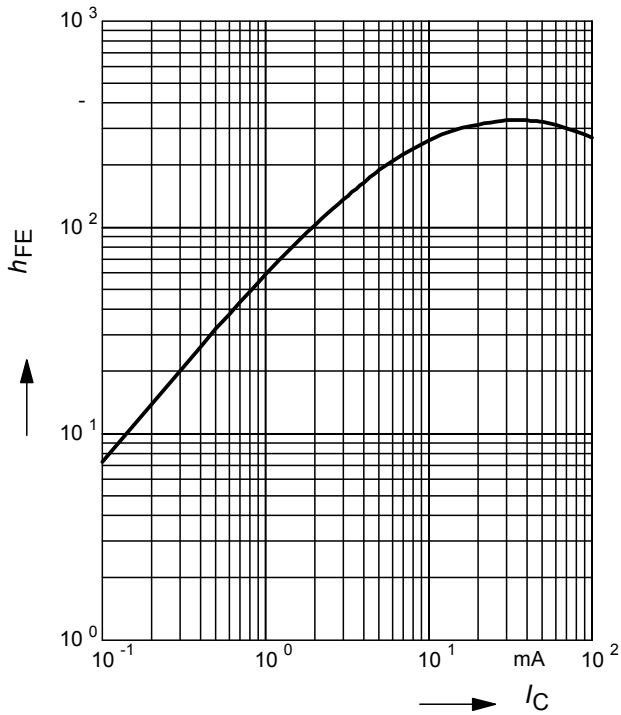
Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

| Parameter | Symbol | Values | | | Unit |
|---|---------------|--------|------|------|------------------|
| | | min. | typ. | max. | |
| DC Characteristics | | | | | |
| Collector-emitter breakdown voltage $I_C = 100 \mu\text{A}, I_B = 0$ | $V_{(BR)CEO}$ | 50 | - | - | V |
| Collector-base breakdown voltage $I_C = 10 \mu\text{A}, I_E = 0$ | $V_{(BR)CBO}$ | 50 | - | - | |
| Collector-base cutoff current $V_{CB} = 40 \text{ V}, I_E = 0$ | I_{CBO} | - | - | 100 | nA |
| Emitter-base cutoff current $V_{EB} = 10 \text{ V}, I_C = 0$ | I_{EBO} | - | - | 164 | μA |
| DC current gain ¹⁾ $I_C = 5 \text{ V}, V_{CE} = 5 \text{ V}$ | h_{FE} | 70 | - | - | - |
| Collector-emitter saturation voltage ¹⁾ $I_C = 10 \text{ mA}, I_B = 0,5 \text{ mA}$ | V_{CEsat} | - | - | 0,3 | V |
| Input off voltage $I_C = 100 \mu\text{A}, V_{CE} = 5 \text{ V}$ | $V_{i(off)}$ | 0,8 | - | 1,5 | |
| Input on voltage $I_C = 2 \text{ mA}, V_{CE} = 0,3 \text{ V}$ | $V_{i(on)}$ | 1 | - | 3 | |
| Input resistor | R_1 | 32 | 47 | 62 | $\text{k}\Omega$ |
| Resistor ratio | R_1/R_2 | 0,9 | 1 | 1,1 | - |
| AC Characteristics | | | | | |
| Transition frequency $I_C = 10 \text{ mA}, V_{CE} = 5 \text{ V}, f = 100 \text{ MHz}$ | f_T | - | 190 | - | MHz |
| Collector-base capacitance $V_{CB} = 10 \text{ V}, f = 1 \text{ MHz}$ | C_{cb} | - | 3 | - | pF |

¹Pulse test: $t < 300 \mu\text{s}$; $D < 2\%$

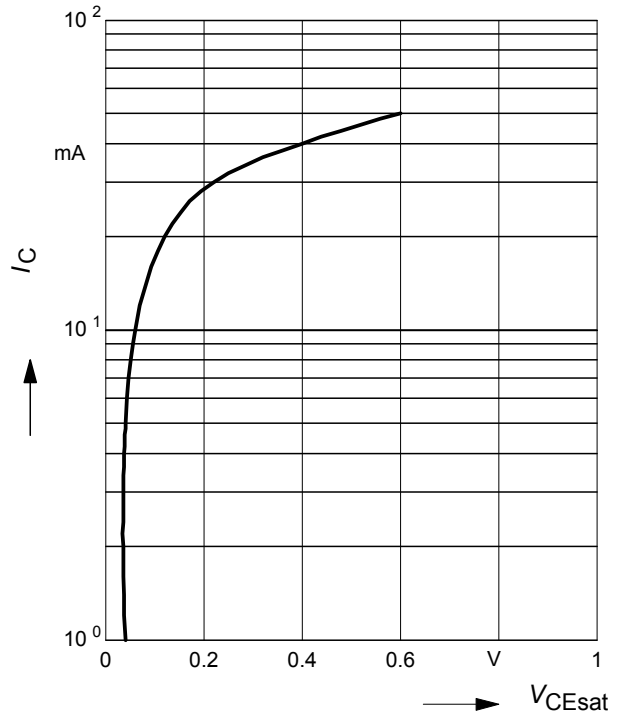
DC current gain $h_{FE} = f(I_C)$

$V_{CE} = 5\text{ V}$ (common emitter configuration)



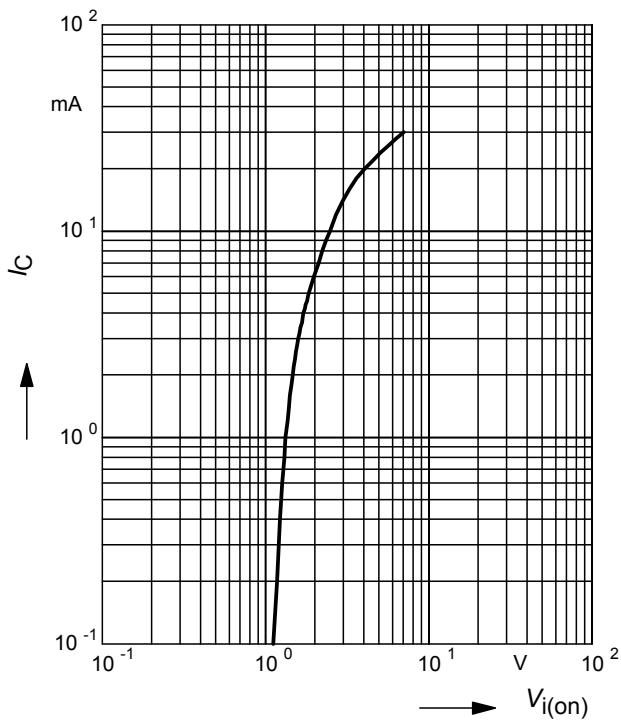
Collector-emitter saturation voltage

$V_{CEsat} = f(I_C), h_{FE} = 20$



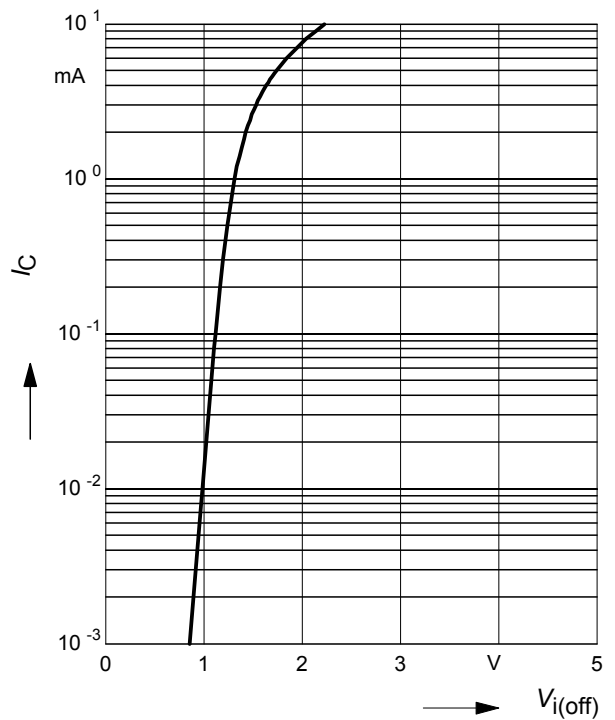
Input on Voltage $V_{i(on)} = f(I_C)$

$V_{CE} = 0.3\text{ V}$ (common emitter configuration)



Input off voltage $V_{i(off)} = f(I_C)$

$V_{CE} = 5\text{ V}$ (common emitter configuration)



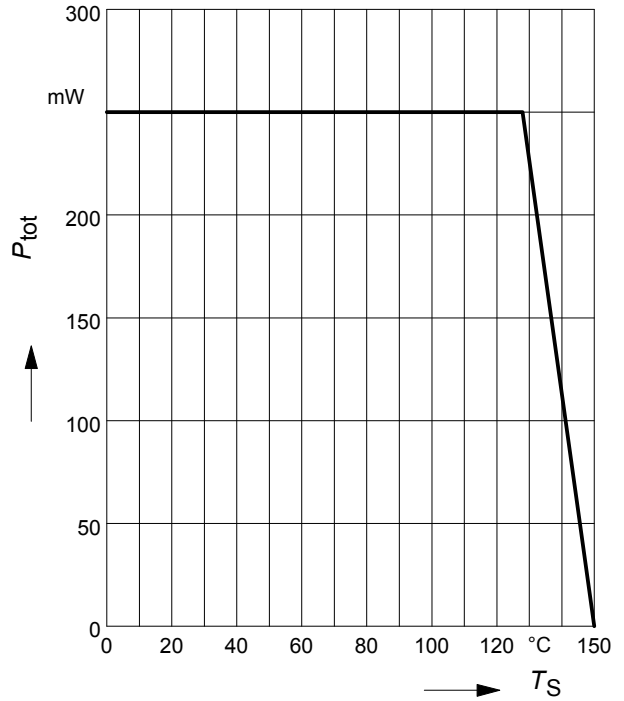
Total power dissipation $P_{tot} = f(T_S)$

BCR198



Total power dissipation $P_{tot} = f(T_S)$

BCR198F



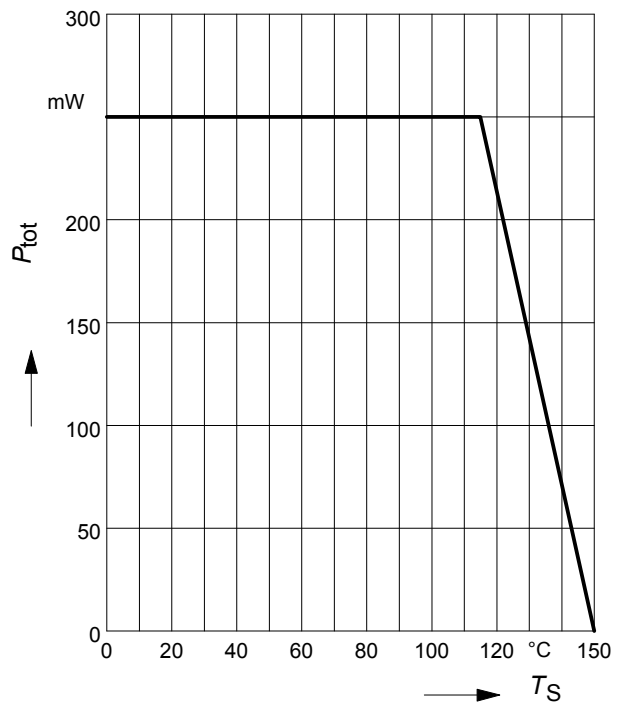
Total power dissipation $P_{tot} = f(T_S)$

BCR198L3



Total power dissipation $P_{tot} = f(T_S)$

BCR198S



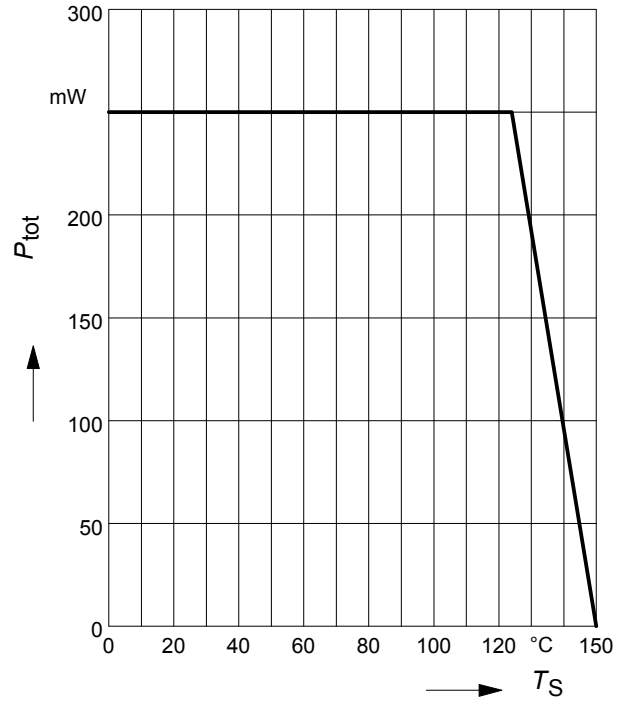
Total power dissipation $P_{tot} = f(T_S)$

BCR198T



Total power dissipation $P_{tot} = f(T_S)$

BCR198W



Total power dissipation $P_{tot} = f(T_S)$

SEMB2



Permissible Pulse Load $R_{thJS} = f(t_p)$

BCR198



Permissible Pulse Load

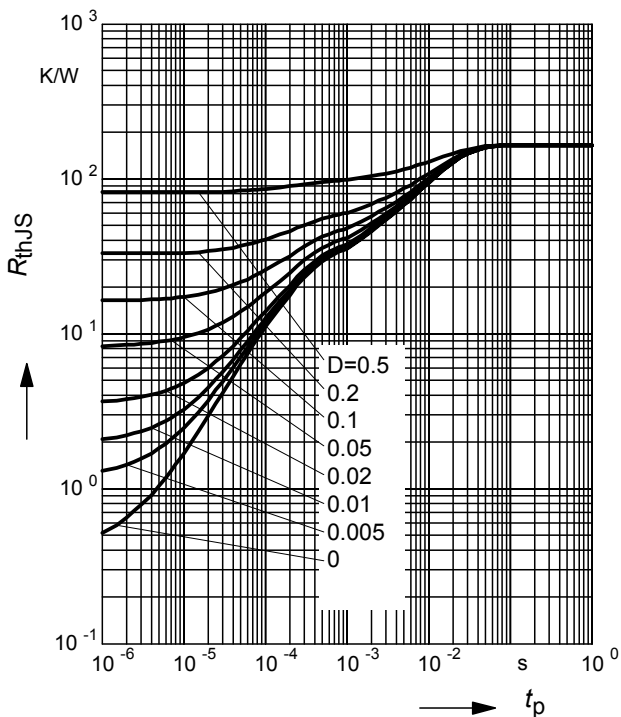
$P_{totmax}/P_{totDC} = f(t_p)$

BCR198



Permissible Puls Load $R_{thJS} = f(t_p)$

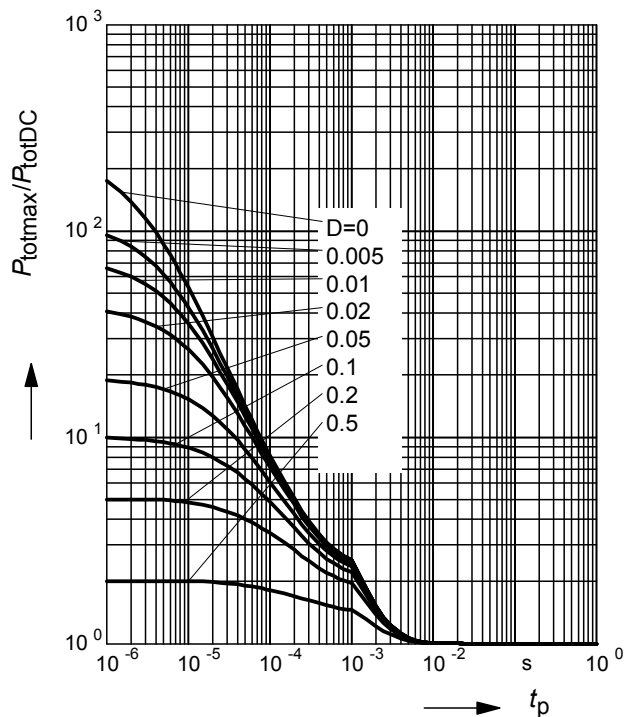
BCR198F



Permissible Pulse Load

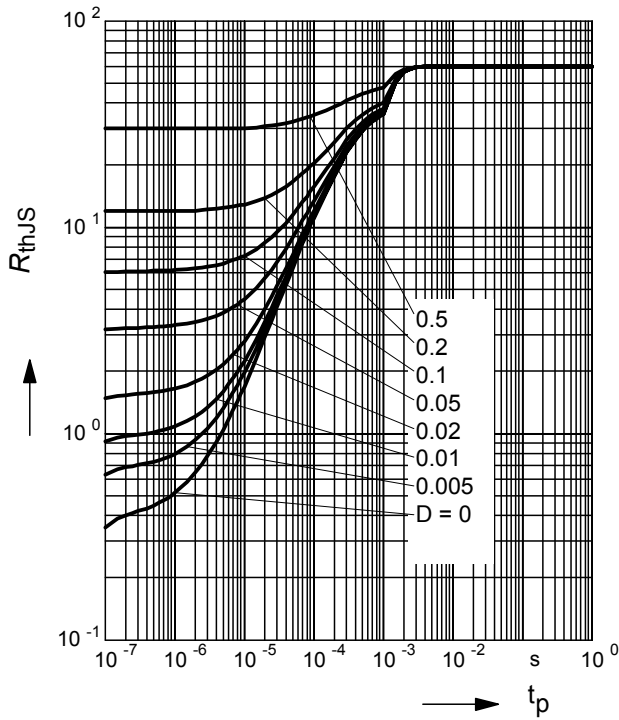
$P_{totmax}/P_{totDC} = f(t_p)$

BCR198F



Permissible Puls Load $R_{thJS} = f(t_p)$

BCR198L3



Permissible Pulse Load

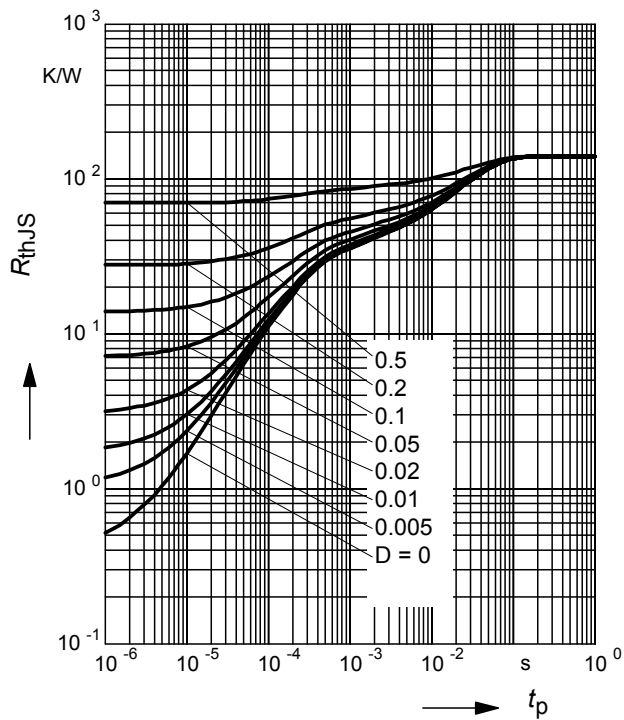
$P_{totmax}/P_{totDC} = f(t_p)$

BCR198L3



Permissible Puls Load $R_{thJS} = f(t_p)$

BCR198S



Permissible Pulse Load

$P_{totmax}/P_{totDC} = f(t_p)$

BCR198S



Permissible Puls Load $R_{thJS} = f(t_p)$

BCR198T



Permissible Pulse Load

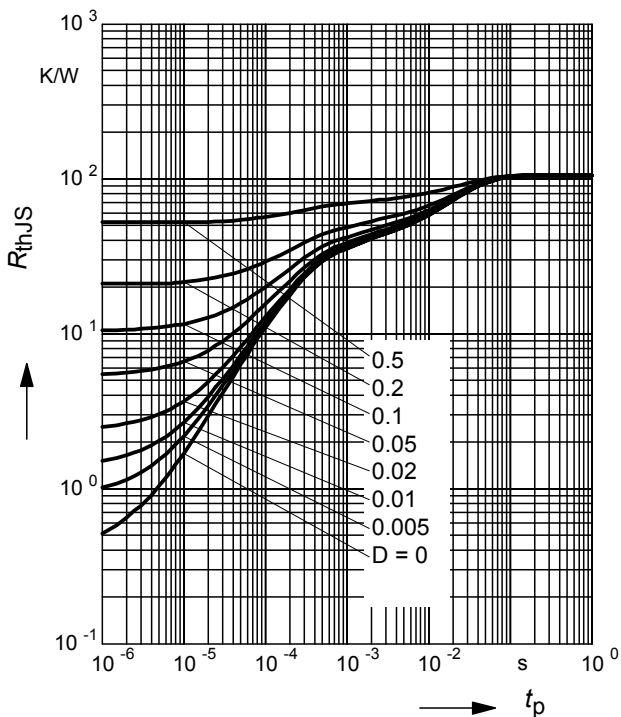
$P_{totmax}/P_{totDC} = f(t_p)$

BCR198T



Permissible Puls Load $R_{thJS} = f(t_p)$

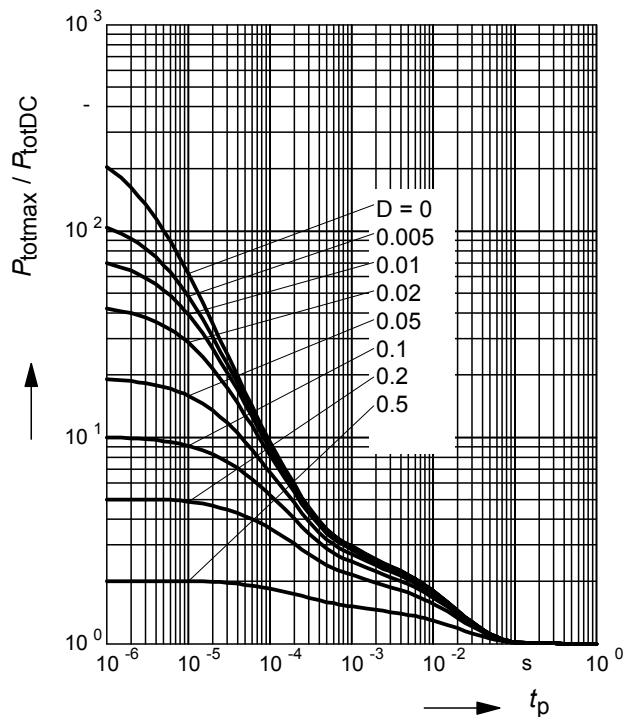
BCR133W



Permissible Pulse Load

$P_{totmax}/P_{totDC} = f(t_p)$

BCR198W



Permissible Puls Load $R_{thJS} = f(t_p)$

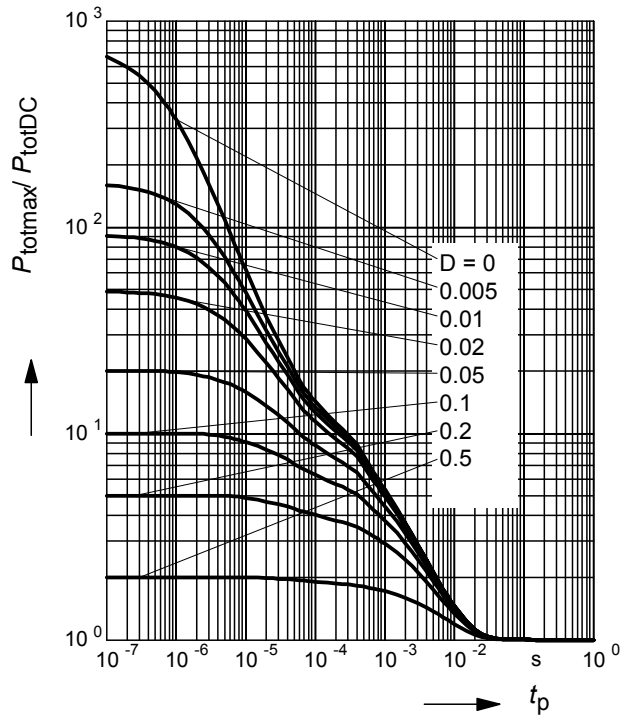
SEMB2



Permissible Pulse Load

$P_{totmax}/P_{totDC} = f(t_p)$

SEMB2



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